



Wireless Components

3-Band TV Tuner IC TUA1030 Version 1.1

Specification January 2002

preliminary

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5-18, 5-19	5-18, 5-19	new definition of thermal properties				

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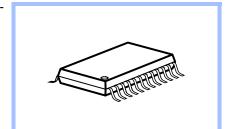
Product Info

Product Info

General Description

The **TUA1030** is a 5 V mixer/oscillator for analog and digital TV and VCR tuners.

Package



Features

General

- Suitable for PAL/NTSC and Digital Video Broadcasting
- Electronic bandswitch
- Local oscillator buffer for external PLL
- Full ESD protection

Mixer/Oscillator

- High impedance mixer input (common emitter) for LOW band
- Low impedance mixer input (common base) for MID and HIGH band

- 2 pin oscillator for LOW band
- 2 pin oscillator for MID band
- 4 pin oscillator for HIGH band

IF-Amplifier

- IF preamplifier with unsymmetrical
 75 Ω output
- External IF filter at the mixer outputs

Application

The IC is suitable for PAL and NTSC tuners in TV- and VCR-sets or set-top receivers for analog TV and Digital Video Broadcasting.

Ordering Information

Туре	Ordering Code	Package
TUA1030	Q67031-A1189	P-TSSOP-24-1

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Product Description

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Product Description

2.1 Overview

The TUA1030 is a mixer/oscillator/IF-amplifier IC suitable for 3-band tuners.

The device includes three double balanced mixers and oscillators for LOW, MID and HIGH band respectively and an IF amplifier. Two pins are available at the mixer output / IF amplifier input to enable IF filtering for improved signal handling.

The LOW, MID and HIGH bands are selected and switched by the SW0 and SW1 inputs $\,$

2.2 Features

General

- Suitable for PAL/NTSC and Digital Video Broadcasting
- Full ESD protection

Mixer/Oscillator

- High impedance mixer input (common emitter) for LOW band
- Low impedance mixer input (common base) for MID and HIGH band
- 2 pin oscillator for LOW band
- 2 pin oscillator for MID band
- 4 pin oscillator for HIGH band

IF-Amplifier

IF preamplifier with unsymmetrical 75 Ω output

2.3 Application

■ The IC is suitable for PAL and NTSC tuners in TV- and VCR-sets or set-top receivers for analog TV and Digital Video Broadcasting.

Confidential Product Description

Recommended band limits in MHz:

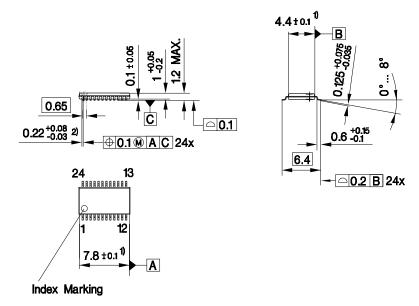
Table 2-1 NTSC tuners					
	RF i	nput	Osci	llator	
	min	max	min	max	
LOW	55.25	127.25	101	173	
MID	133.25	361.25	179	407	
HIGH	367.25	801.25	413	847	

Table 2-2 PAL tuners					
	RF input Oscillate			llator	
	min	max	min	max	
LOW	44.25	154.25	83.15	193.15	
MID	161.25	439.25	200.15	478.15	
HIGH	447.25	863.25	486.15	902.15	

Note: Tuning margin of ± 3 MHz not included.

2.4 Package Outlines

P-TSSOP-24-1

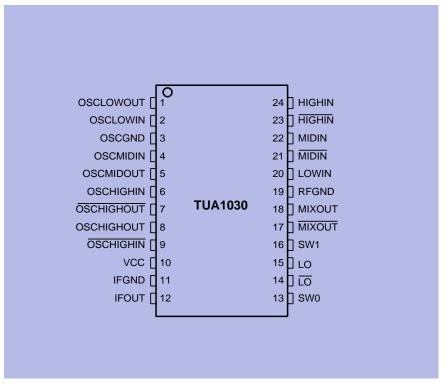


- 1) Does not include plastic or metal protrusion of 0.15 max. per side
- 2) Does not include dambar protrusion of 0.08 max. per side

Con	tents of this Chapter
3.1	Pin Configuration
3.2	Pin Definition and Function
3.3	Block Diagram
3.4	Circuit Description

Functional Description

3.1 Pin Configuration



Pin Config

Functional Description



Confidential

3.2 Pin Definition and Function

Table	Table 3-1 Pin Definition and Function					
Pin	Symbol	Equivalent I/O-Schematic	Aver	age DC vo	ltage	
No.			LOW	MID	HIGH	
1	OSCLOWOUT		2.2 V			
		1				
2	OSCLOWIN	2	1.5 V			
3	OSCGND	oscillator ground	0.0 V	0.0 V	0.0 V	
4	OSCMIDIN			1.5 V		
		5				
5	OSCMIDOUT			2.2 V		



Table	Table 3-1 Pin Definition and Function (continued)						
Pin No.	Symbol	Equivalent I/O-Schematic	Aver	age DC vo	ltage		
			LOW	MID	HIGH		
6	OSCHIGHIN				1.8 V		
		Д Д					
7	OSCHIGOUT	Y Y			2.2 V		
		7 - 8					
8	OSCHIGOUT	6 9			2.2 V		
9	OSCHIGHIN	T T			1.8 V		
		Ų					
		-					
10	VCC	supply voltage	5.0 V	5.0 V	5.0 V		
11	IFGND	IF ground	0.0 V	0.0 V	0.0 V		
12	IFOUT		2.1 V	2.1 V	2.1 V		
		- √ ∧					
		12					
13	SW0		3 V to	0 V to	0 V to		
10	OWO	Т	V _{CC}	1.5 V	1.5 V		
		ф					
		Ĭ					
		13					
		בי					
		r					
							
14	LO		2.5 V	2.5 V	2.5 V		
15	LO	[*]	2.5 V	2.5 V	2.5 V		
		14, 15					



Table	Table 3-1 Pin Definition and Function (continued)					
Pin No.	Symbol	Equivalent I/O-Schematic	Aver	age DC vo	ltage	
			LOW	MID	HIGH	
16	SW1	16	0 V to 1.5 V	3 V to Vcc	0 V to 1.5 V	
17	MIXOUT	ļ ļ	4.0 V	4.0 V	4.0 V	
18	MIXOUT	17 Oscillator	4.0 V	4.0 V	4.0 V	
19	RFGND	IF ground	0.0 V	0.0 V	0.0 V	
20	LOWIN	34	1.9 V			



Table	Table 3-1 Pin Definition and Function (continued)						
Pin	Symbol	Equivalent I/O-Schematic	Average DC voltage				
No.			LOW	MID	HIGH		
21	MIDIN			0.75 V	0.75 V		
22	MIDIN	20		0.75 V	0.75 V		
23	HIGHIN			0.75 V	0.75 V		
24	HIGHIN	23 24		0.75 V	0.75 V		

Functional Description



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3.3 Block Diagram

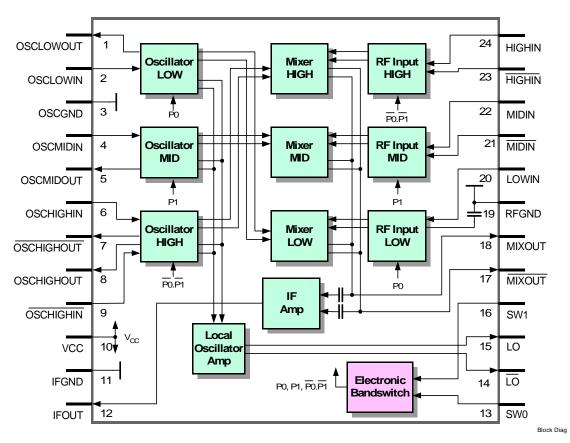


Figure 3-1 **Block Diagram**

3.4 Circuit Description

The **TUA1030** is a mixer/oscillator/IF-amplifier IC suitable for 3-band tuners.

The device includes three balanced mixers (one mixer with an unbalanced highimpedance input and two mixers with a balanced low-impedance input), two 2pin asymmetrical oscillators for the LOW and the MID band, one 4-pin symmetrical oscillator for the HIGH band, an IF amplifier, a reference voltage, and a band switch. Two pins are available at the mixer output / IF amplifier input to enable IF filtering for improved signal handling.

The LOW, MID and HIGH bands are selected and switched by the SW0 and SW1 inputs

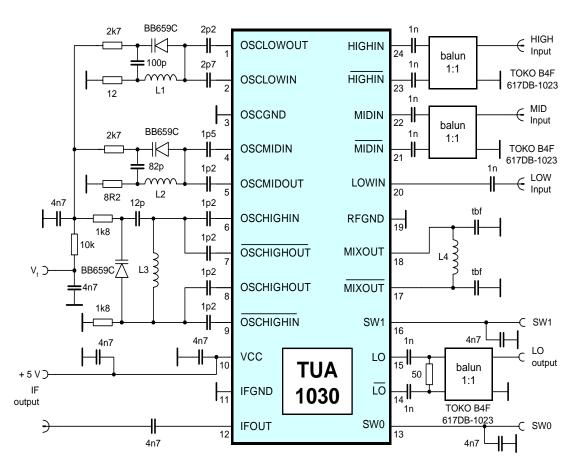
4 Applications

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Confidential Applications

4.1 Circuits

4.1.1 Application Circuit for NTSC



App_circuit_ntsc

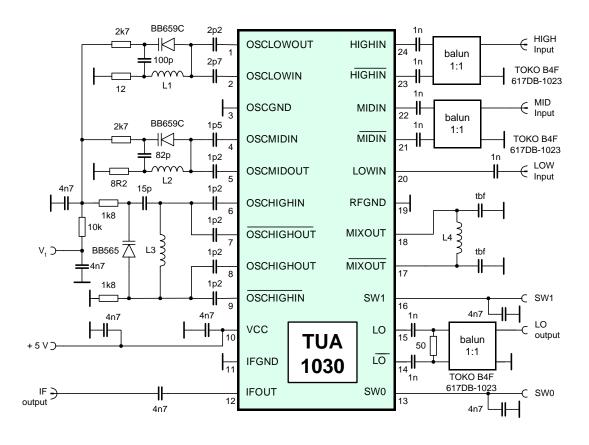
Figure 4-1 Application Circuit for NTSC

Recommended band limits in MHz										
	RF i	nput	Oscillator							
	min	max	min	max						
LOW	55.25	127.25	101	173						
MID	133.25	361.25	179	407						
HIGH	367.25	801.25	413	847						

	C	oils	
	turns	Ø	wire Ø
L1	8.5	3.2 mm	0.5 mm
L2	3.5	2.5 mm	0.5 mm
L3	1.5	2.4 mm	0.5 mm
L4	12.5	3.5 mm	0.3 mm

Applications

4.1.2 Application Circuit for PAL



App_circuit

Figure 4-2 Application Circuit for PAL

Recommended band limits in MHz										
	RF i	nput	Oscillator							
	min	max	min	max						
LOW	44.25	154.25	83.15	193.15						
MID	161.25	439.25	200.15	478.15						
HIGH	447.25	863.25	486.15	902.15						

	C	oils	
	turns	Ø	wire Ø
L1	8.5	3.2 mm	0.5 mm
L2	2.5	3 mm	0.5 mm
L3	1.5	2.4 mm	0.5 mm
L4	14.5	4 mm	0.3 mm

5 Reference

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Reference

5.1 Electrical Data

5.1.1 Absolute Maximum Ratings



WARNING

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC may result.

Table 5-1 Absolute Maximum Rati	ngs, ambient te	emperatu	re T _{AMB} = ·	-10°C + 85°C	
Parameter ^{1).}	Symbol	Limit	Values	Unit	Remarks
		min	max		
Supply voltage	V _{CC}	-0.3	6	V	
Ambient temperature	T _A	-10	T _{Amax} 2).	°C	
Storage temperature	T _{Stg}	-40	+125	°C	
Junction temperature	T _J		+ 125	°C	
Temperature difference junction to case ^{3).}	T _{JC}		2	K	
Mixer-Oscillator					
Mix inputs LOW band	V_{LOW}	-0.3	3	V	
Mix inputs MID band	V_{MID}		2	V	
	I _{MID}	-5	6	mA	
Mix inputs HIGH band	V _{HIGH}		2	V	
	I _{HIGH}	-5	6	mA	
VCO base voltage	V _B	-0.3	3	V	LOW, MID and HIGH band oscillators
VCO collector voltage	V _C		6	V	LOW, MID and HIGH band oscillators
ESD-Protection ^{4).}					
all pins	V _{ESD}		2	kV	

^{1).} All values are referred to ground (pin), unless stated otherwise. Currents with a positive sign flow into the pin and currents with a negative sign flow out of the pin.

- 2). The maximum ambient temperature depends on the mounting conditions of the package. Any application mounting must guarantee not to exceed the maximum junction temperature of 125 °C. As reference the temperature difference junction to case is given.
- 3). Referred to top center of package.
- 4). According to EIA/JESD22-A114-B (HBM in-circuit test), as a single device in-circuit contact discharge test.

5.1.2 Operating Range

Within the operating range the IC operates as described in the circuit description. The AC / DC characteristic limits are not guaranteed.

Table 5-2 Operating Range											
Parameter	Symbol	Limit Values		Unit	Test Conditions	L	Item				
		min	max								
Supply voltage	V _{CC}	+4.5	+5.5	V							
LOW mixer input frequency range	f _{MIXL}	30	200	MHz							
MID and HIGH band mixer input frequency range	f _{MIXM/H}	130	900	MHz							
LOW oscillator frequency range	f _{OL}	65	250	MHz							
MID band oscillator frequency range	f _{OM}	165	530	MHz							
HIGH band oscillator frequency range	f _{OH}	400	950	MHz							
Ambient temperature	T _{AMB}	-10	T _{Amax} 1).	°C							

^{1).} see 5.1.1 Absolute Maximum Ratings on page 19

5.1.3 AC/DC Characteristics

Table 5-3 AC/DC Characteristics with T _{AMB} = 25 °C, V _{CC} = 5 V									
	Symbol	Limit Values		Unit	Test Conditions	L Item			
		min	typ	max					
Supply									
Supply voltage	V _{CC}	4.5	5	5.5	V				
Current consumption	Icc		48		mA	LOW band			
	I _{CC}		50		mA	MID band			
	Icc		41		mA	HIGH band			

Analog Part

LOW band mixer mode (SW0 = 1, SW	1 = 0, incl	uding IF a	amplifier)			
RF frequency	f _{RF}	44.25		161.25	MHz	picture carrier 1).	
Voltage gain	G _V	18	21	24	dB	f _{RF} = 44.25 MHz,	
						see 5.3.1 on page 30	
	G _V	18	21	24	dB	f _{RF} = 161.25 MHz,	
						see 5.3.1 on page 30	
Noise figure	NF		8	10	dB	$f_{RF} = 50 \text{ MHz},$	
						see 5.3.3 on page 31, see 5.3.4 on page 31	
Outrot veltere en enviere	\ / \	400	444		-ID. AV		
Output voltage causing 0.3% of crossmodulation	Vo	108	111		dBµV	f _{RF} = 44.25 MHz, see 5.3.6 on page 32	
in channel	V	108	111		dBµV	f _{RF} = 161.25 MHz,	
	V _O	100	111		αБμν	see 5.3.6 on page 32	
Output voltage causing	Vo	108	111		dBµV	f _{RF} = 44.25 MHz ^{2).}	
1.1 kHz incidental FM							
	Vo	108	111		dΒμV	f _{RF} = 161.25 MHz ^{2.)}	
750 Hz Pulling	V _i	88			dΒμV	f _{RF} = 154.25 MHz ^{3).}	
Channel S02 beat	INT _{S02}	57	60		dBc	V _{RFpix} = 115 dBμV	
						at IF output ^{4).}	
Channel A-5 beat	INT _{A-5}	57	60		dBc	V _{RFpix} = 115 dBμV	
						at IF output ^{5).}	
Channel CH6 color beat	INT _{CH6}	63	66		dBc	V _{RFpix} = 80 dBμV	
<u> </u>						$V_{RFsnd} = 80 \text{ dB}\mu V^{6)}$.	



Table 5-3 AC/DC Charac	teristics wit	h T _{AMB} = 2	25 °C, V _{CC}	= 5 V (cc	ntinued			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Input conductance	9 _i		1		mS	f _{RF} = 44.25 MHz, see 5.2.1 on page 27		
	g _i		1		mS	f _{RF} = 161.25 MHz, see 5.2.1 on page 27		
Input capacitance	C _i		1		pF	f _{RF} = 44.25 to 161.25 MHz, see 5.2.1 on page 27		
MID band mixer mode (S	W0 = 0, SW1	=1, inclu	ding IF an	nplifier)				
RF frequency	f _{RF}	157		454.25		picture carrier 1.)		
Voltage gain	G _V	28	31	34	dB	f _{RF} = 157 MHz, see 5.3.2 on page 30		
	G _V	28	31	34	dB	f _{RF} = 454.25 MHz, see 5.3.2 on page 30		
Noise figure (not corrected for image)	NF		6	8	dB	f _{RF} = 157 MHz, see 5.3.5 on page 32		
	NF		6	8	dB	f _{RF} = 300 MHz, see 5.3.5 on page 32		
Output voltage causing 0.3% of crossmodulation	Vo	108	111		dΒμV	f _{RF} = 157 MHz, see 5.3.7 on page 33		
in channel	Vo	108	111		dΒμV	f _{RF} = 454.25 MHz, see 5.3.7 on page 33		
Output voltage causing	V _O	108	111		dΒμV	f _{RF} = 157MHz ^{2.)}		
1.1 kHz incidental FM	Vo	108	111		dΒμV	f _{RF} = 454.25 MHz ^{2.)}		
N+5 - 1 MHz pulling	N+5 - 1 MHz	77	80		dΒμV	f _{RFw} = 443 MHz, f _{OSC} = 481.9 MHz, f _{RFu} = 482 MHz ^{7).}		
750 Hz Pulling	V _i	78			dΒμV	f _{RF} = 439.25 MHz ^{3.)}		
Input impedance $Z_i = (R_s + j\omega L_s)$	R _s		35		Ω	f _{RF} = 157 MHz, see 5.2.2 on page 27		
	R _s		35		Ω	f _{RF} = 454.25 MHz, see 5.2.2 on page 27		
	L _s		8		nH	f _{RF} = 157 MHz, see 5.2.2 on page 27		
	L _s		8		nH	f _{RF} = 454.25 MHz, see 5.2.2 on page 27		



Table 5-3 AC/DC Charac	teristics wit	h T _{AMB} = 2	25 °C, V _C (_C = 5 V (co	ntinued			
	Symbol	Li	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
HIGH band mixer mode (SW0 = 0, SW	1 = 0, inc	luding IF	amplifier)				
RF frequency	f _{RF}	443		863.25		picture carrier 1.)		
Voltage gain	G _V	28	31	34	dB	f _{RF} = 443 MHz, see 5.3.2 on page 30		
	G _V	28	31	34	dB	f _{RF} = 863.25 MHz, see 5.3.2 on page 30		
Noise figure (not corrected for image)	NF		6	8	dB	f _{RF} = 443.25 MHz, see 5.3.5 on page 32		
	NF		7	9	dB	f _{RF} = 863.25 MHz, see 5.3.5 on page 32		
Output voltage causing 0.3% of crossmodulation in channel	V _O	108	111		dΒμV	f _{RF} = 443.25 MHz, see 5.3.7 on page 33		
in channel	V _O	108	111		dΒμV	f _{RF} = 863.25 MHz, see 5.3.7 on page 33		
Output voltage causing	V _O	108	111		dΒμV	f _{RF} = 443.25 MHz ^{2.)}		
1.1 kHz incidental FM	V _O	108	111		dΒμV	f _{RF} = 863.25 MHz ^{2.)}		
N+5 - 1 MHz pulling	N+5 - 1 MHz	77	80		dΒμV	f _{RFw} = 863.25 MHz, f _{OSC} = 902.15 MHz, f _{RFu} = 902.25 MHz ^{7.)}		
750 Hz Pulling	V _i	78			dΒμV	f _{RF} = 855.25 MHz ^{3.)}		
Input impedance $Z_i = (R_s + j\omega L_s)$	R _s		35		Ω	f _{RF} = 443 MHz, see 5.2.2 on page 27		
	R _s		35		Ω	f _{RF} = 863.25 MHz, see 5.2.2 on page 27		
	L _s		8		nH	f _{RF} = 443 MHz, see 5.2.2 on page 27		
	L _s		8		nH	f _{RF} = 863.25 MHz, see 5.2.2 on page 27		
LOW band oscillator, see	Chapter 4							
Oscillator frequency	fosc	83.15		207	MHz	8).		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5 \% ^{9)}$.		
	$\Delta f_{OSC(V)}$		110		kHz	$\Delta V_{CC} = 10 \% ^{9.)}$		



Table 5-3 AC/DC Characteristics with T _{AMB} = 25 °C, V _{CC} = 5 V (continued)								
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Oscillator frequency drift	$\Delta f_{OSC(T)}$		800	1000	kHz	$\Delta T = 25 ^{\circ}\text{C},$ with compensation ^{10).}		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		500	700	kHz	5 s to 15 min after switch on ^{11).}		
Phase noise, carrier to noise sideband	$\Phi_{ ext{OSC}}$	87	92		dBc/ Hz	±10 kHz frequency off- set, worst case in fre- quency range		
	$\Phi_{ ext{OSC}}$	107	112		dBc/ Hz	±100 kHz frequency offset, worst case in frequency range		
Ripple susceptibility of V _P (peak-to-peak value)	RSC	15	20		mV	4.75 V < VP < 5.25 V, worst case in frequency range, ripple frequency 500 kHz ^{12).}		
MID band oscillator, see	Chapter 4							
Oscillator frequency	f _{OSC}	195.7		500	MHz	8.)		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5 \%^{9.)}$		
	$\Delta f_{OSC(V)}$		110		kHz	$\Delta V_{CC} = 10 \% ^{9.)}$		
Oscillator frequency drift	$\Delta f_{OSC(T)}$		800	1000	kHz	$\Delta T = 25$ °C; with compensation ^{10.)}		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		500	700	kHz	5 s to 15 min after switch on ^{11.)}		
Phase noise, carrier to noise sideband	Φ_{OSC}	85	90		dBc/ Hz	±10 kHz frequency off- set, worst case in fre- quency range		
	Φ_{OSC}	105	110		dBc/ Hz	±100 kHz frequency offset, worst case in frequency range		
Ripple susceptibility of V _P (peak-to-peak value)	RSC	15	20		mV	4.75 < VP < 5.25 V, worst case in frequency range, ripple frequency 500 kHz ^{12.)}		
HIGH band oscillator, see	e Chapter 4							
Oscillator frequency	fosc	481.9		902.15	MHz	8.)		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5 \% ^{9.)}$		
	$\Delta f_{OSC(V)}$		300		kHz	ΔV _{CC} = 10 % ^{9.)}		
Oscillator frequency drift	$\Delta f_{OSC(T)}$		1100	1500	kHz	$\Delta T = 25$ °C; with compensation ^{10.)}		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		600	900	kHz	5 s to 15 min after switch on ^{11).}		



Table 5-3 AC/DC Charac	teristics wit	h T _{AMB} = 2	25 °C, V _C (= 5 V (cc	ontinued			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Phase noise, carrier to noise sideband	Φ_{OSC}	85	90		dBc/ Hz	±10 kHz frequency off- set, worst case in fre- quency range		
	$\Phi_{\sf OSC}$	105	110		dBc/ Hz	±100 kHz frequency offset, worst case in frequency range		
Ripple susceptibility of V _P (peak-to-peak value)	RSC	15	20		mV	4.75 < VP < 5.25 V, worst case in frequency range, ripple frequency 500 kHz ^{14.)}		
IF amplifier								
Mixer output impedance $Y_0 = Gs + j\omega C_s$	R _i		3		kΩ	at 36 MHz, see 5.2.4 on page 28		
	C _i		4		pF	at 36 MHz, see 5.2.4 on page 28		
Output impedance $Z_0 = (R_S + j\omega L_S)$	R _S			80	Ω	at 36 MHz, see 5.2.5 on page 29		
	L _S		7		nH	at 36 MHz, see 5.2.5 on page 29		
LO output								
Output admittance YLO	Gp		tbf		mS	at 83.15 MHz		
(Gp//Cp)	Gp		tbf		mS	at 902.15 MHz		
	Ср		tbf		pF			
Output voltage into 50 Ω resistor	V_{LO}	80	91	100	dΒμV			
Spurious signal at LO output referred to LO output signal	S _{RF}			-10	dB			
Band switch inputs SW0	and SW1							
LOW level input voltage	V _{SWL}	0		1.5	V			
HIGH level input voltage	V _{SWH}	3		V _{CC}	V			
Input current	I _{SW}			10	μA			

[■] This value is only guaranteed in lab.

- 1). The RF frequency range is defined by the oscillator frequency range and the intermediate frequency (IF).
- 2). This is the level of the RF unwanted signal (50% amplitude modulated with 1kHz) that causes a 1.1 kHz FM modulation of the local oscillator and thus of the wanted signal; $V_{wanted} = 100 \text{ dB}\mu\text{V}$; $f_{unwanted} = f_{wanted} + 5.5 \text{ MHz}$.
- 3). This is the level of the RF signal (100% amplitude modulated with 11.89 kHz) that causes a 750 Hz frequency deviation on the oscillator signal producing sidebands 30 dB below the level of the oscillator signal.

Reference

- 4). Channel S02 beat is the interfering product of f_{RFpix} , f_{IF} and f_{OSC} of channel S02, f_{BEAT} = 37.35 MHz. The possible mechanisms are f_{OSC} 2 x f_{IF} or 2 x f_{RFpix} f_{OSC} .
- 5). Channel A-5 beat is the interfering product of f_{RFpix} , f_{IF} and f_{OSC} of channel A-5; f_{BEAT} = 45.5 MHz. The possible mechanisms are: f_{OSC} 2 x f_{IF} or 2 x f_{RFpix} f_{OSC} .
- 6). Channel 6 beat is the interfering product of $f_{RFpix} + f_{RFsnd} f_{OSC}$ of channel 6 at 42 MHz.
- 7). N+5 -1 MHz is defined as the input level of channel N+5, at frequency 1 MHz lower, causing FM sidebands 30 dB below the wanted carrier.
- 8). Limits are related to the tank circuit used in the application board (see Chapter 4). Frequency bands may be adjusted by the choice of external components.
- 9). The frequency shift is defined as a change in oscillator frequency when the supply voltage varies from V_{CC} = 5 to 4.75 V (4.5 V) or from V_{CC} = 5 to 5.25 V (5.5 V). The oscillator is free running during this measurement.
- 10). The frequency drift is defined as a change in oscillator frequency when the ambient temperature varies from $T_{amb} = 25$ to 50 °C or from $T_{amb} = 25$ to 0 °C. The oscillator is free running during this measurement.
- 11). The switch-on drift is defined as a change in oscillator frequency between 5 s and 15 min after switch-on. The oscillator is free running during this measurement.
- 12). The supply ripple susceptibility is measured in the application board (see Chapter 4), using a spectrum analyser connected to the IF output. An unmodulated RF signal is applied to the test board RF input. A sinewave signal with a frequency of 500 kHz is superposed onto the supply voltage (see 5.3.8 on page 33). The amplitude of this ripple is adjusted to bring the 500 kHz sidebands around the IF carrier to a level of 53.5 dBc with respect to the carrier.

5.1.4 Band Selection

Table 5-4 Internal band selection	Table 5-5	Table 5-6
Band	SW0	SW1
LOW	+ 5 V	0 V or open
MID	0 V or open	+ 5 V
HIGH ^{1).}	0 V or open	0 V or open

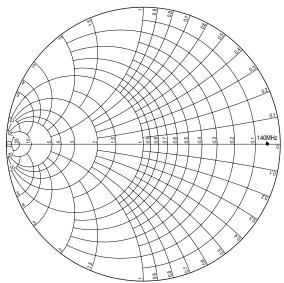
1). This is the default mode at power-on.

Reference

5.2 Electrical Diagrams

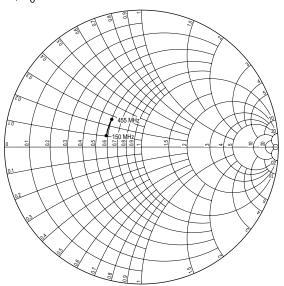
5.2.1 Input admittance (S11) of the LOW band mixer

40 to 170 MHz, $Y_0 = 20mS$



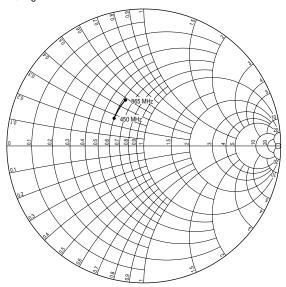
5.2.2 Input impedance (S11) of the MID band mixer

150 to 455 MHz, $Z_0 = 50 \Omega$



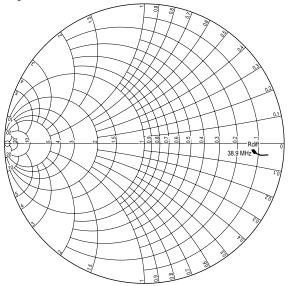
5.2.3 Input impedance (S11) of the HIGH band mixer

450 to 865 MHz, Z_0 = 50 Ω



5.2.4 Output admittance (S22) of the of the Mixer output

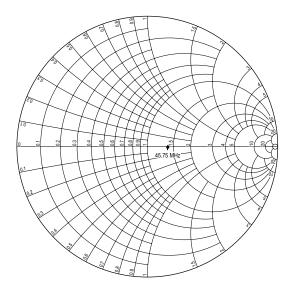
30 to 50 MHz, $Y_0 = 20mS$



Reference

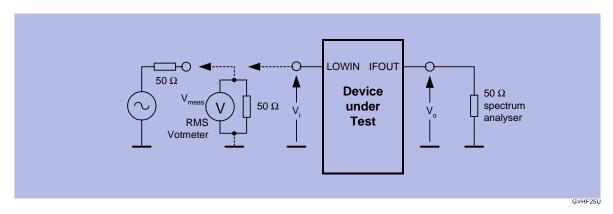
5.2.5 Output impedance (S22) of the IF output

$$Z_0 = 50 \Omega$$



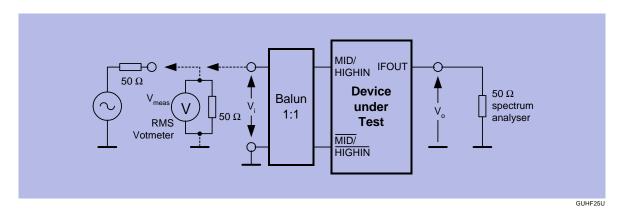
5.3 Measurement Circuits

5.3.1 Gain (G_V) measurement in LOW band



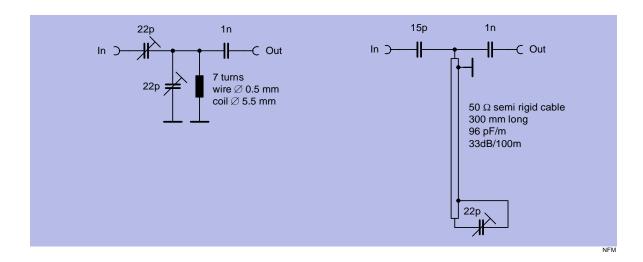
- $Z_i >> 50 Ω => V_i = 2 x V_{meas} = 80 dBμV$
- $V_i = V_{meas} + 6dB = 80 dB\mu V$
- $G_V = 20 \log(V_0 / V_i)$

5.3.2 Gain (G_V) measurement in MID and HIGH bands



- $V_i = V_{meas} = 70 \text{ dB}\mu\text{V}$
- $G_v = 20 \log(V_0 / V_i) + 1 dB (1 dB = insertion loss of balun)$

5.3.3 Matching circuit for optimum noise figure in LOW band



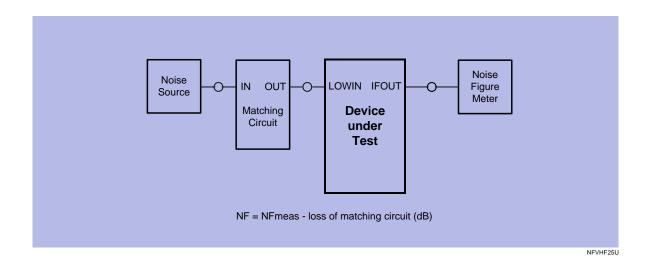
For $f_{RF} = 50 \text{ MHz}$

- loss = 0 dB
- image suppression = 16 dB

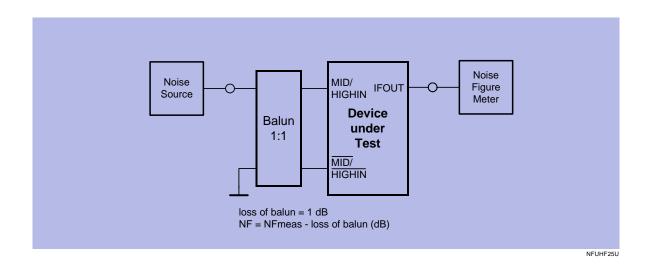
For $f_{RF} = 150 \text{ MHz}$

- loss = 1.4 dB
- image suppression = 13 dB

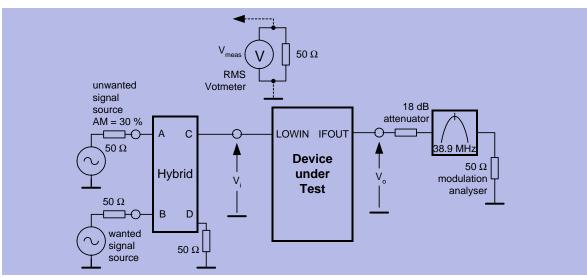
5.3.4 Noise figure (NF) measurement in LOW band



5.3.5 Noise figure (NF) measurement in MID and HIGH bands



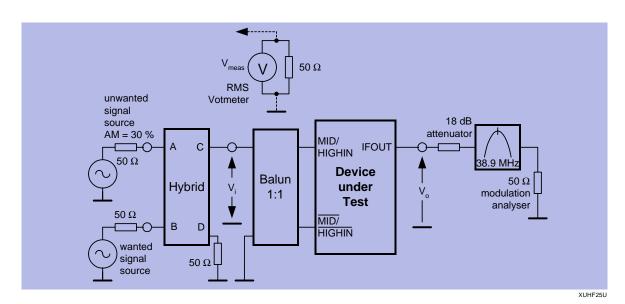
5.3.6 Cross modulation measurement in LOW band



XVHF25U

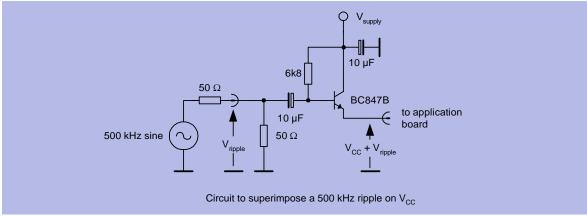
- $Z_i >> 50 \Omega => V_i = 2 \times V_{meas}$
- wanted output signal at f_{pix}, V_o = 100 dBµV
- unwanted output signal at f_{snd}

5.3.7 Cross modulation measurement in MID and HIGH bands



- wanted output signal at f_{pix}, V_o = 100 dBµV
- unwanted output signal at f_{snd}

5.3.8 Ripple susceptibility measurement



RIF